

LM148QML

Quad 741 Op Amps

General Description

The LM148 is a true quad LM741. It consists of four independent, high gain, internally compensated, low power operational amplifiers which have been designed to provide functional characteristics identical to those of the familiar LM741 operational amplifier. In addition the total supply current for all four amplifiers is comparable to the supply current of a single LM741 type op amp. Other features include input offset currents and input bias current which are much less than those of a standard LM741. Also, excellent isolation between amplifiers has been achieved by independently biasing each amplifier and using layout techniques which minimize thermal coupling.

The LM148 can be used anywhere multiple LM741 or LM1558 type amplifiers are being used and in applications where amplifier matching or high packing density is required.

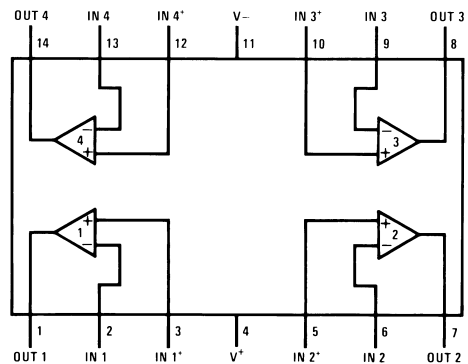
Features

- 741 op amp operating characteristics
- Class AB output stage—no crossover distortion
- Pin compatible with the LM124
- Overload protection for inputs and outputs
- Low supply current drain: 0.6 mA/Amplifier
- Low input offset voltage: 1 mV
- Low input offset current: 4 nA
- Low input bias current: 30 nA
- High degree of isolation between amplifiers: 120 dB
- Gain bandwidth product (unity gain): 1.0 MHz

Ordering Information

| NS PART NUMBER | SMD PART NUMBER | NS PACKAGE NUMBER | PACKAGE DESCRIPTION |
|----------------|-----------------|-------------------|----------------------------|
| LM148E/883 | | E20A | 20LD LEADLESS CHIP CARRIER |
| LM148J/883 | | J14A | 14LD CERDIP |

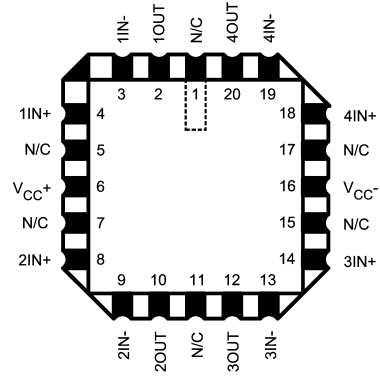
Connection Diagrams



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Top View
See NS Package Number J14A

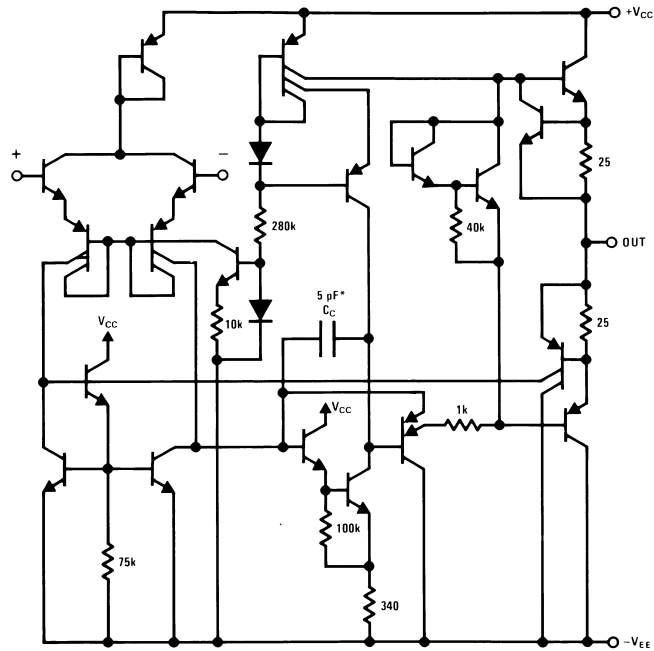
Connection Diagrams (Continued)



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Top View
See NS Package Number E20A

Schematic Diagram



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* 1 pF in the LM149

Absolute Maximum Ratings (Note 1)

| | |
|---|------------------------|
| Supply Voltage | ±22V |
| Differential Input Voltage | ±44V |
| Output Short Circuit Duration(Note 2) | Continuous |
| Power Dissipation (P_d at 25°C) (Note 3) | 1100mW |
| Thermal Resistance | |
| θ_{JA} | |
| CERDIP (Still Air) | 103°C/W |
| CERDIP (500LF/ Min Air flow) | 52°C/W |
| LCC (Still Air) | 90°C/W |
| LCC (500LF/ Min Air flow) | 66°C/W |
| θ_{JC} | |
| CERDIP | 19°C/W |
| LCC | 21°C/W |
| Maximum Junction Temperature (T_{jMAX}) | 150°C |
| Operating Temperature Range | -55°C ≤ T_A ≤ +125°C |
| Storage Temperature Range | -65°C ≤ T_A ≤ +150°C |
| Lead Temperature (Soldering, 10 sec.) Ceramic | 300°C |
| ESD tolerance (Note 4) | 500V |

Quality Conformance Inspection

MIL-STD-883, Method 5005 — Group A

| Subgroup | Description | Temp (°C) |
|----------|---------------------|------------|
| 1 | Static tests at | +25 |
| 2 | Static tests at | +125 |
| 3 | Static tests at | -55 |
| 4 | Dynamic tests at | +25 |
| 5 | Dynamic tests at | +125 |
| 6 | Dynamic tests at | -55 |
| 7 | Functional tests at | +25 |
| 8A | Functional tests at | +125 |
| 8B | Functional tests at | -55 |
| 9 | Switching tests at | +25 |
| 10 | Switching tests at | +125 |
| 11 | Switching tests at | -55 |

Electrical Characteristics

DC PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.) $V_{CC} = \pm 15V$, $R_S = 0\Omega$

| Symbol | Parameter | Conditions | Notes | Min | Max | Units | Sub-groups |
|--------------|------------------------------|--|----------|-----|-----|-------|------------|
| V_{IO} | Input Offset Voltage | $V_{CM} = 0V$, $R_S = 50\Omega$ | | -5 | +5 | mV | 1 |
| | | | | -6 | +6 | mV | 2,3 |
| I_{IO} | Input Offset Current | $V_{CM} = 0V$ | | -25 | +25 | nA | 1 |
| | | | | -75 | +75 | nA | 2,3 |
| $\pm I_{IB}$ | Input Bias Current | $V_{CM} = 0V$ | | 1 | 100 | nA | 1 |
| | | | | 1 | 325 | nA | 2,3 |
| R_{in} | Input Resistance | | (Note 5) | 0.8 | | MΩ | 1 |
| PSRR+ | Power Supply Rejection Ratio | $+V_{CC} = +15V$ and $+5V$, $-V_{CC} = -15V$, $R_S = 50\Omega$ | | 77 | | dB | 1, 2, 3 |
| PSRR- | Power Supply Rejection Ratio | $+V_{CC} = +15V$, $-V_{CC} = -15V$ and $-5V$, $R_S = 50\Omega$ | | 77 | | dB | 1, 2, 3 |

Electrical Characteristics (Continued)

DC PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.) $V_{CC} = \pm 15V$, $R_S = 0\Omega$

| Symbol | Parameter | Conditions | Notes | Min | Max | Units | Sub-groups |
|------------|-----------------------------|---|-------|-----|-----|-------|------------|
| CMRR | Common Mode Rejection Ratio | $+V_{CM} = \pm 12V$, $R_S = 50\Omega$ | | 70 | | dB | 1, 2, 3 |
| I_{OS+} | Short Circuit Current | | | -55 | -14 | mA | 1 |
| I_{OS-} | Short Circuit Current | | | 14 | 55 | mA | 1 |
| I_{CC} | Power Supply Current | | | 0.4 | 3.6 | mA | 1 |
| | | | | 0.4 | 4.5 | mA | 2, 3 |
| A_{VS+} | Large Signal Voltage Gain | $V_{OUT} = 0V$ to $+10V$, $R_L > 2\text{ k}\Omega$ | | 50 | | V/mV | 4 |
| | | | | 25 | | V/mV | 5, 6 |
| A_{VS-} | Large Signal Voltage Gain | $V_{OUT} = 0V$ to $-10V$, $R_L > 2\text{ k}\Omega$ | | 50 | | V/mV | 4 |
| | | | | 25 | | V/mV | 5, 6 |
| V_{out+} | Output Voltage Swing | $R_L = 10\text{ k}\Omega$ | | +12 | | V | 4, 5, 6 |
| | | $R_L = 2\text{ k}\Omega$ | | +10 | | V | 4, 5, 6 |
| V_{out-} | Output Voltage Swing | $R_L = 10\text{ k}\Omega$ | | | -12 | V | 4, 5, 6 |
| | | $R_L = 2\text{ k}\Omega$ | | | -10 | V | 4, 5, 6 |

Electrical Characteristics

AC PARAMETERS (The following conditions apply to all parameters, unless otherwise specified.) $V_{CC} = \pm 15V$, $A_V = 1$, $R_S = 0\Omega$

| Symbol | Parameter | Conditions | Notes | Min | Max | Units | Sub-groups |
|----------|------------------------|------------|-------|-----|-----|------------|------------|
| $\pm SR$ | Slew Rate | | | 0.2 | | V/ μs | 7, 8A, 8B |
| G_{BW} | Gain Bandwidth Product | | | 0.4 | 1.4 | MHz | 7, 8A, 8B |

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

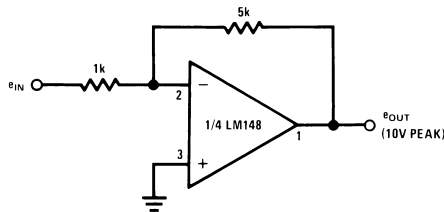
Note 2: Any of the amplifier outputs can be shorted to ground indefinitely; however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.

Note 3: The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T_{JMAX} , θ_{JA} , and the ambient temperature, T_A . The maximum available power dissipation at any temperature is $P_d = (T_{JMAX} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is less.

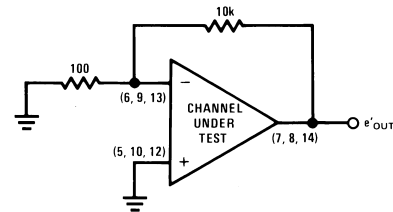
Note 4: Human body model, 1.5 k Ω in series with 100 pF

Note 5: Parameter Guaranteed, Not Tested.

Cross Talk Test Circuit $V_S = \pm 15V$

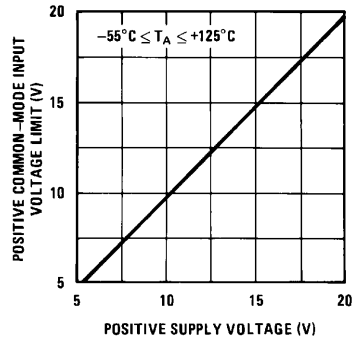


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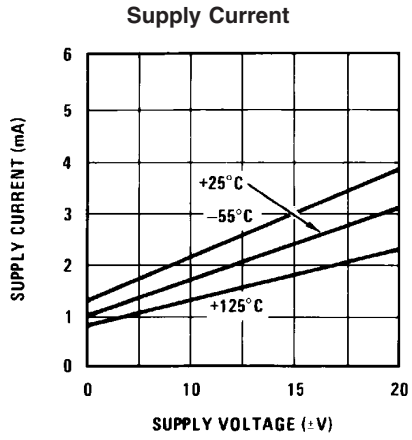
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Cross Talk Test Circuit $V_S = \pm 15V$ (Continued)

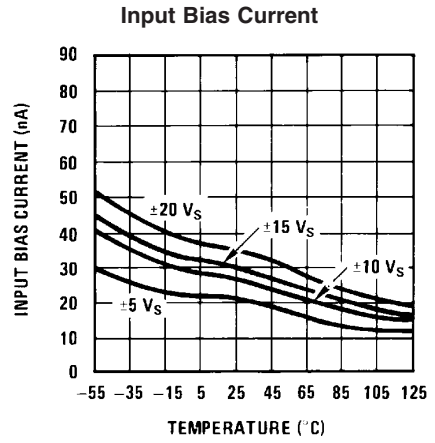


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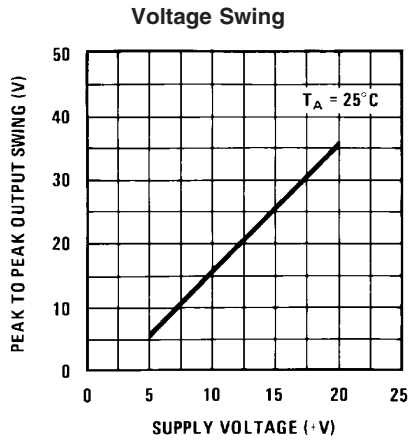
Typical Performance Characteristics



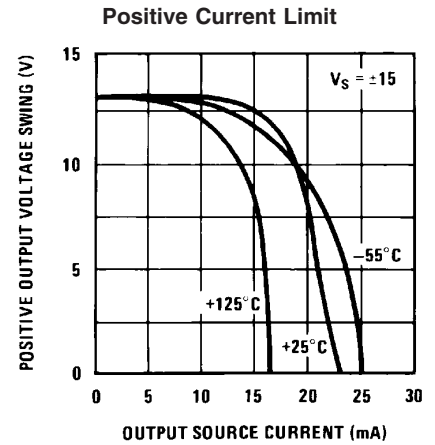
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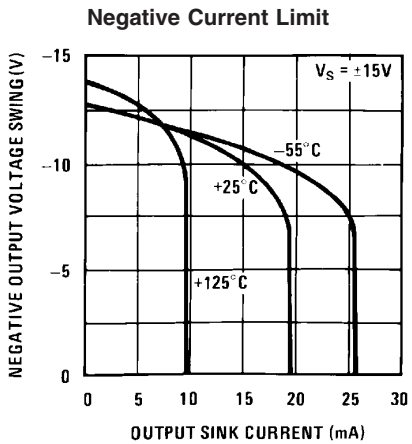
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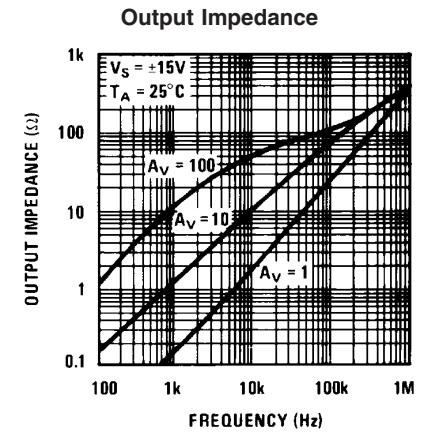
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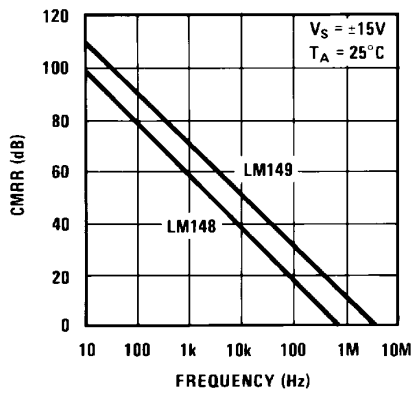
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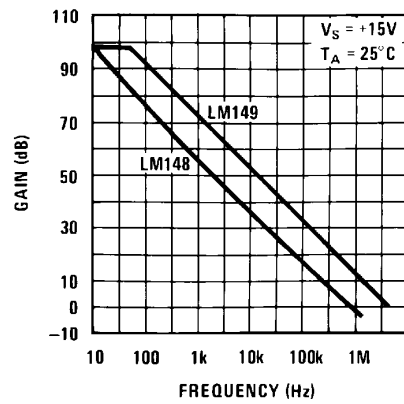
Typical Performance Characteristics (Continued)

Common-Mode Rejection Ratio



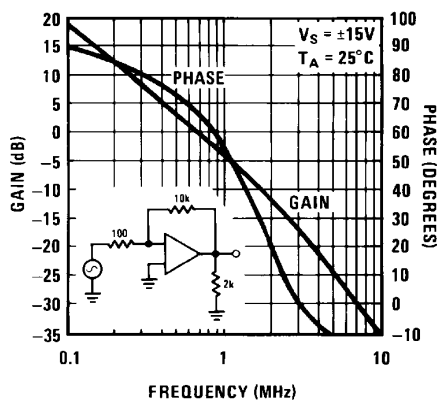
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Open Loop Frequency Response



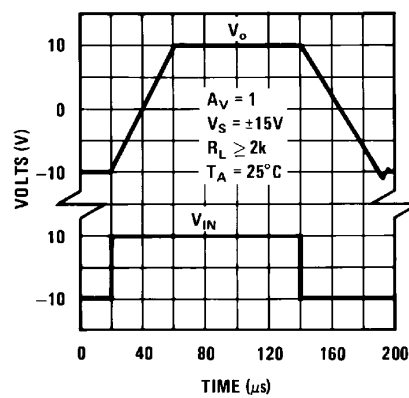
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Bode Plot LM148



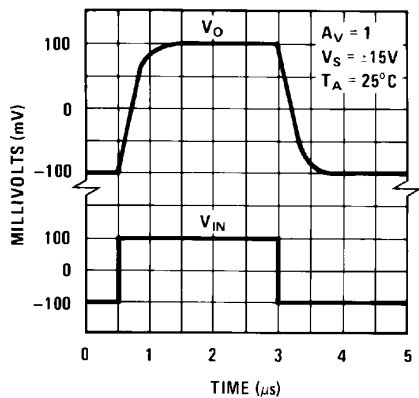
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Large Signal Pulse Response (LM148)



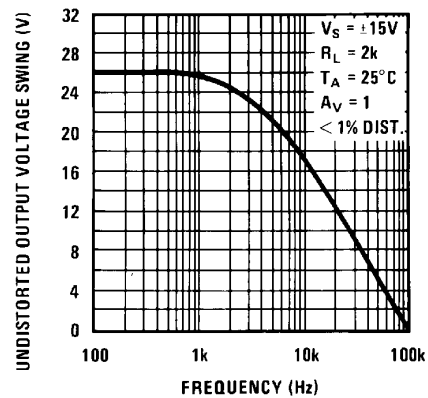
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Small Signal Pulse Response (LM148)



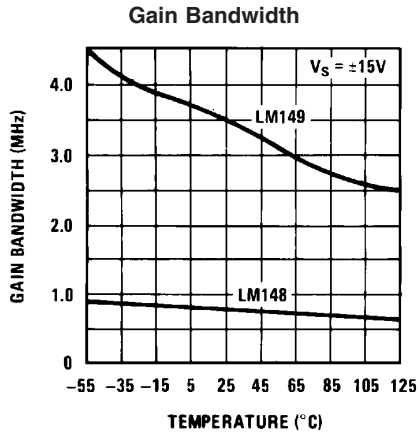
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Undistorted Output Voltage Swing

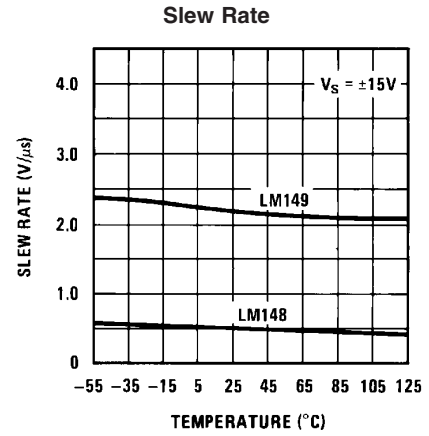


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Typical Performance Characteristics (Continued)

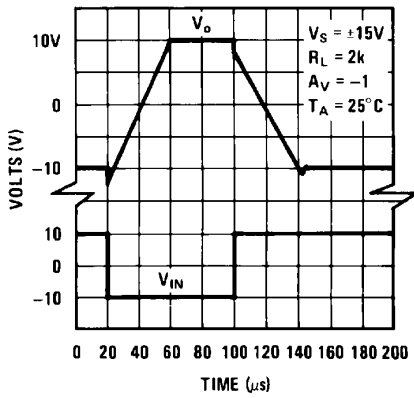


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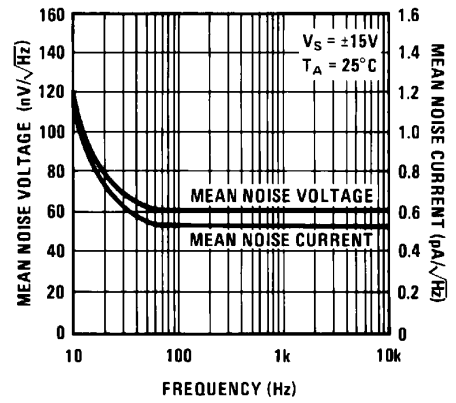
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Inverting Large Signal Pulse Response (LM148)



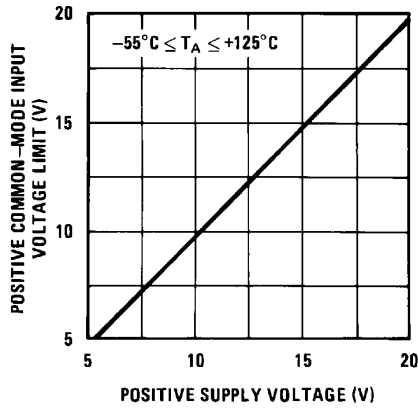
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Input Noise Voltage and Noise Current



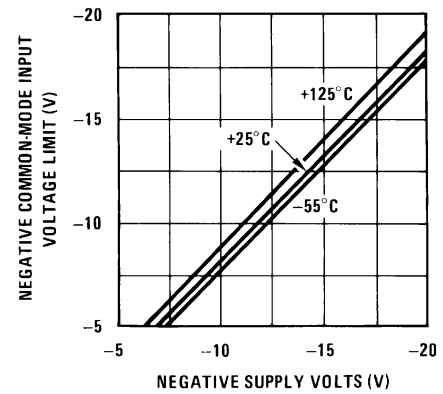
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Positive Common-Mode Input Voltage Limit



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Negative Common-Mode Input Voltage Limit



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Application Hints

The LM148 series are quad low power LM741 op amps. In the proliferation of quad op amps, these are the first to offer the convenience of familiar, easy to use operating characteristics of the LM741 op amp. In those applications where LM741 op amps have been employed, the LM148 series op amps can be employed directly with no change in circuit performance.

The package pin-outs are such that the inverting input of each amplifier is adjacent to its output. In addition, the amplifier outputs are located in the corners of the package which simplifies PC board layout and minimizes package related capacitive coupling between amplifiers.

The input characteristics of these amplifiers allow differential input voltages which can exceed the supply voltages. In addition, if either of the input voltages is within the operating common-mode range, the phase of the output remains correct. If the negative limit of the operating common-mode range is exceeded at both inputs, the output voltage will be positive. For input voltages which greatly exceed the maximum supply voltages, either differentially or common-mode, resistors should be placed in series with the inputs to limit the current.

Like the LM741, these amplifiers can easily drive a 100 pF capacitive load throughout the entire dynamic output voltage and current range. However, if very large capacitive loads must be driven by a non-inverting unity gain amplifier, a resistor should be placed between the output (and feedback

connection) and the capacitance to reduce the phase shift resulting from the capacitive loading.

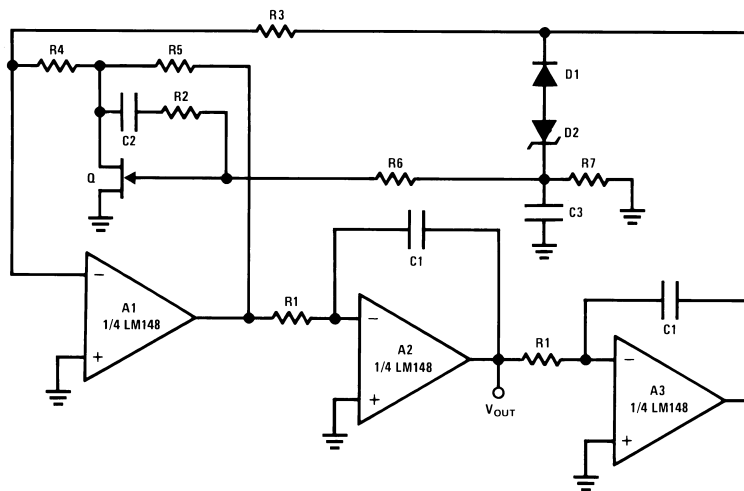
The output current of each amplifier in the package is limited. Short circuits from an output to either ground or the power supplies will not destroy the unit. However, if multiple output shorts occur simultaneously, the time duration should be short to prevent the unit from being destroyed as a result of excessive power dissipation in the IC chip.

As with most amplifiers, care should be taken lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pickup" and maximize the frequency of the feedback pole which capacitance from the input to ground creates.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

Typical Applications—LM148

One Decade Low Distortion Sinewave Generator



20120508

$$f = \frac{1}{2\pi R_1 C_1} \times \sqrt{K}, K = \frac{R_4 R_5}{R_3} \left(\frac{1}{r_{DS}} + \frac{1}{R_4} + \frac{1}{R_5} \right), r_{DS} \approx \frac{R_{ON}}{\left(1 - \frac{V_{GS}}{V_P} \right)^{1/2}}$$

$f_{MAX} = 5$ kHz, THD $\leq 0.03\%$

$R_1 = 100k$ pot. $C_1 = 0.0047$ μ F, $C_2 = 0.01$ μ F, $C_3 = 0.1$ μ F, $R_2 = R_6 = R_7 = 1M$,

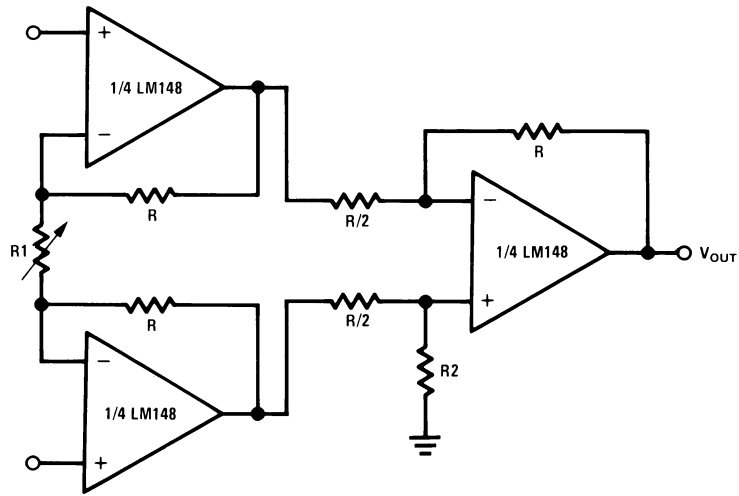
$R_3 = 5.1k$, $R_4 = 12\Omega$, $R_5 = 240\Omega$, $Q = NS5102$, $D_1 = 1N914$, $D_2 = 3.6V$ avalanche

diode (ex. LM103), $V_S = \pm 15V$

A simpler version with some distortion degradation at high frequencies can be made by using A1 as a simple inverting amplifier, and by putting back to back zeners in the feedback loop of A3.

Typical Applications—LM148 (Continued)

Low Cost Instrumentation Amplifier



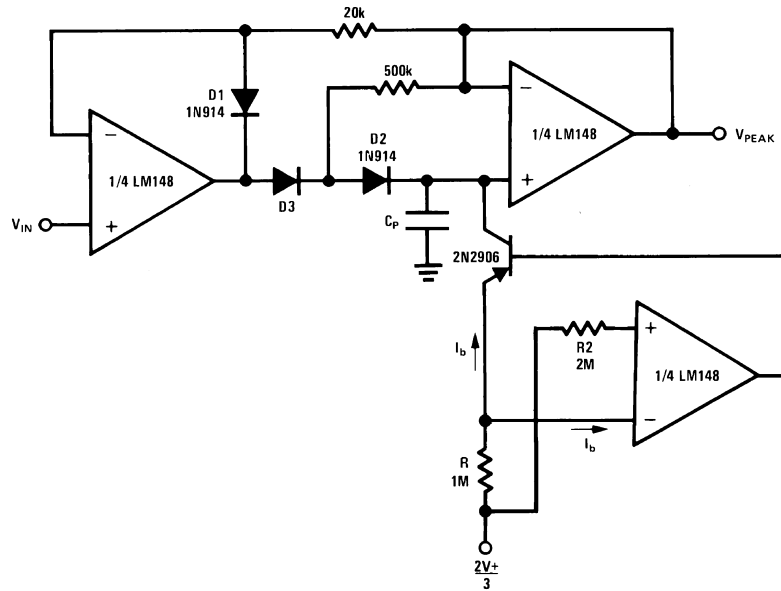
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$$V_{OUT} = 2 \left(\frac{2R}{R1} + 1 \right) \cdot V_S - 3V \leq V_{IN\ CM} \leq V_S^+ - 3V,$$

$V_S = \pm 15V$

$R = R2$, trim $R2$ to boost CMRR

Low Drift Peak Detector with Bias Current Compensation

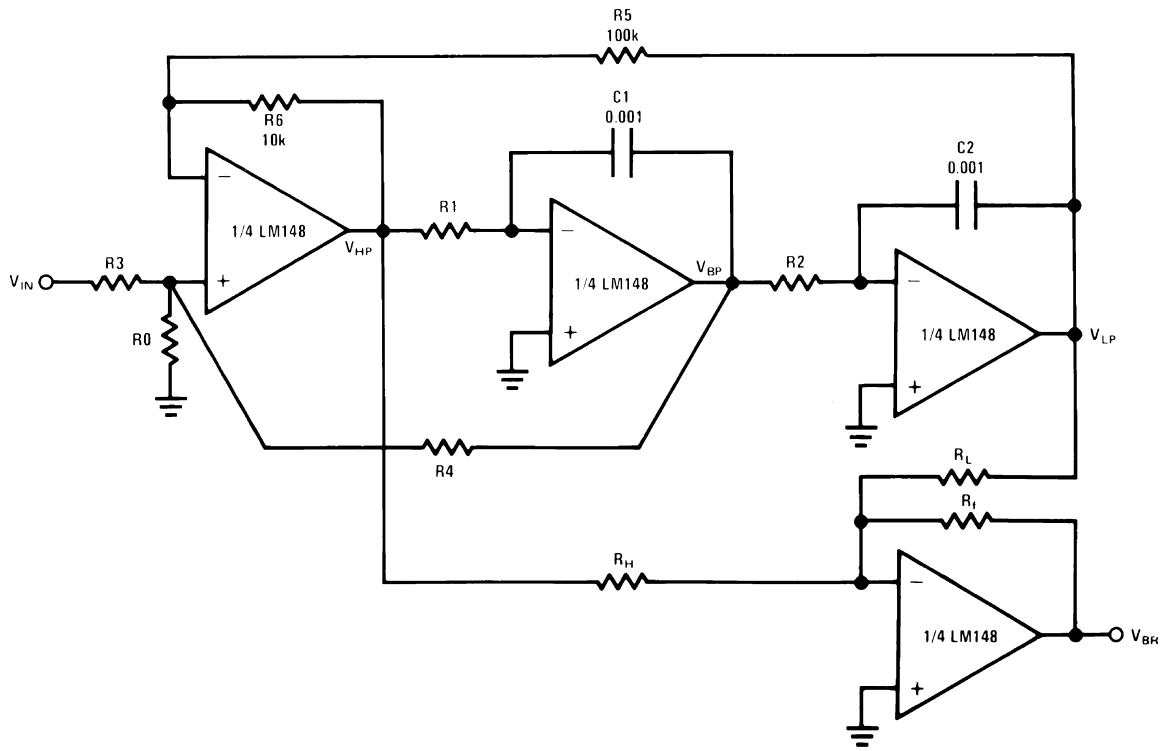


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Adjust R for minimum drift
 D3 low leakage diode
 D1 added to improve speed
 $V_S = \pm 15V$

Typical Applications—LM148 (Continued)

Universal State-Variable Filter



Tune Q through R0,
 For predictable results: $f_o Q \leq 4 \times 10^4$
 Use Band Pass output to tune for Q

20120511

$$\frac{V(s)}{V_{IN}(s)} = \frac{N(s)}{D(s)}, D(s) = s^2 + \frac{s\omega_o}{Q} + \omega_o^2$$

$$N_{HP}(s) = s^2 H_{OHP}, N_{BP}(s) = \frac{-s\omega_o H_{OBP}}{Q}, N_{LP} = \omega_o^2 H_{OLP}$$

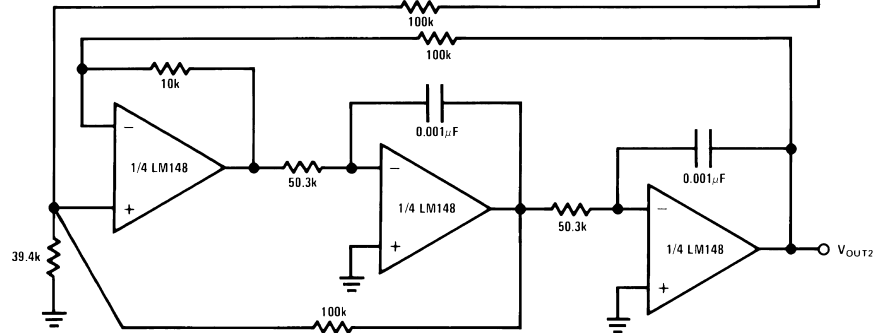
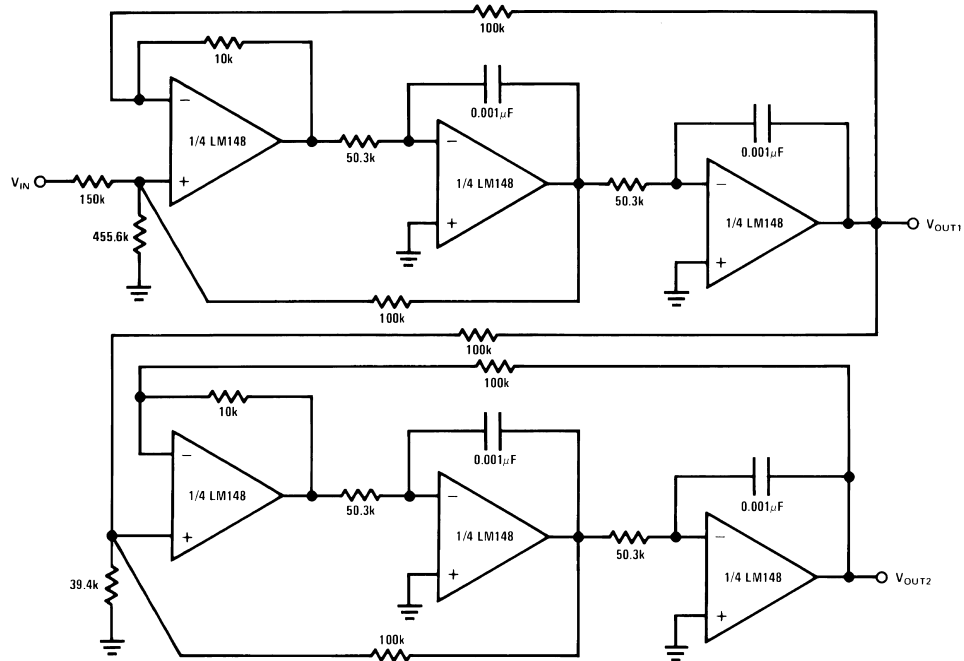
$$f_o = \frac{1}{2\pi} \sqrt{\frac{R6}{R5}} \sqrt{\frac{1}{t_1 t_2}}, t_i = R_i C_i, Q = \left(\frac{1 + R4|R3 + R4|R0}{1 + R6|R5} \right) \left(\frac{R6 t_1}{R5 t_2} \right)^{1/2}$$

$$f_{NOTCH} = \frac{1}{2\pi} \left(\frac{R_H}{R_L t_1 t_2} \right)^{1/2}, H_{OHP} = \frac{1 + R6|R5}{1 + R3|R0 + R3|R4}, H_{OBP} = \frac{1 + R4|R3 + R4|R0}{1 + R3|R0 + R3|R4}$$

$$H_{OLP} = \frac{1 + R5|R6}{1 + R3|R0 + R3|R4}$$

Typical Applications—LM148 (Continued)

A 1 kHz 4 Pole Butterworth



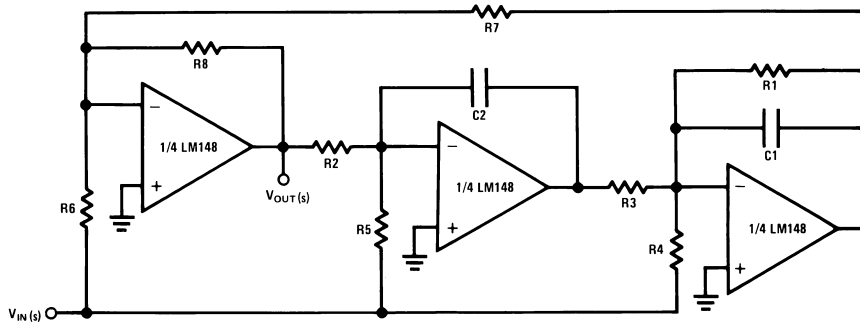
Use general equations, and tune each section separately

$Q_{1stSECTION} = 0.541$, $Q_{2ndSECTION} = 1.306$

The response should have 0 dB peaking

20120512

A 3 Amplifier Bi-Quad Notch Filter



20120513

$$Q = \sqrt{\frac{R8}{R7}} \times \frac{R1C1}{\sqrt{R3C2R2C1}}, \quad f_o = \frac{1}{2\pi} \sqrt{\frac{R8}{R7}} \times \frac{1}{\sqrt{R2R3C1C2}}, \quad f_{NOTCH} = \frac{1}{2\pi} \sqrt{\frac{R6}{R3R5R7C1C2}}$$

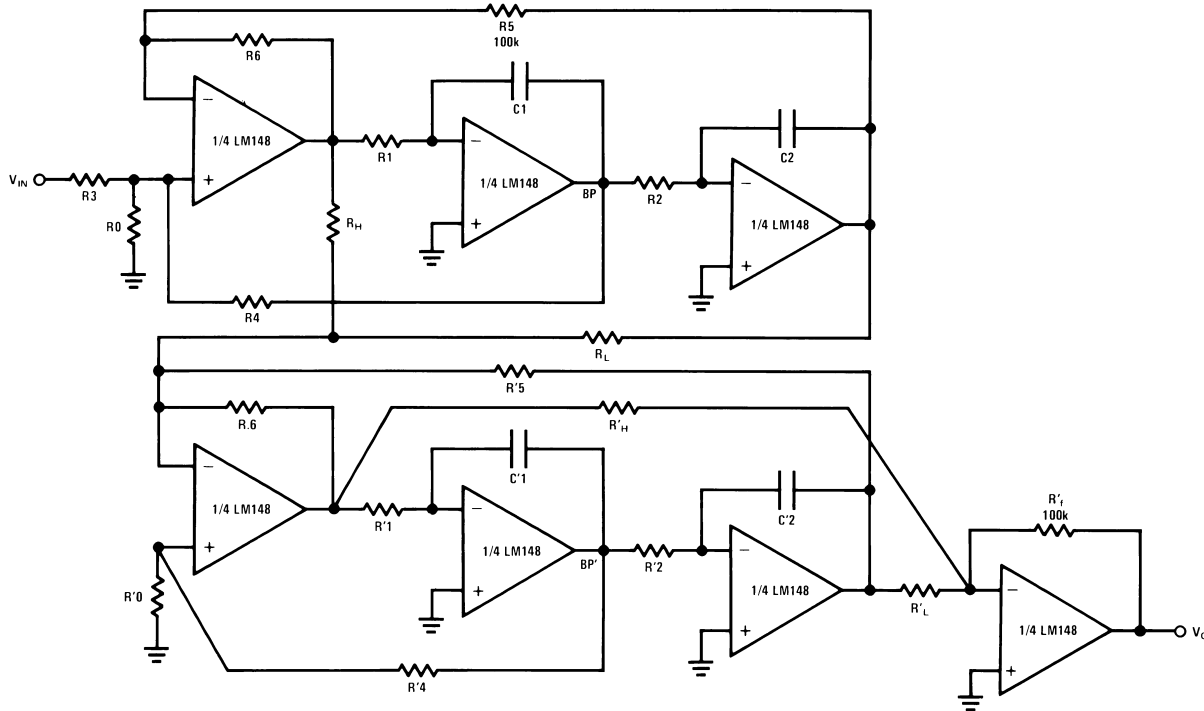
$$\text{Necessary condition for notch: } \frac{1}{R6} = \frac{R1}{R4R7}$$

Ex: $f_{NOTCH} = 3 \text{ kHz}$, $Q = 5$, $R1 = 270k$, $R2 = R3 = 20k$, $R4 = 27k$, $R5 = 20k$, $R6 = R8 = 10k$, $R7 = 100k$, $C1 = C2 = 0.001 \mu\text{F}$

Better noise performance than the state-space approach.

Typical Applications—LM148 (Continued)

A 4th Order 1 kHz Elliptic Filter (4 Poles, 4 Zeros)



20120514

$R1C1 = R2C2 = t$
 $R'1C'1 = R'2C'2 = t'$

$f_c = 1 \text{ kHz}$, $f_s = 2 \text{ kHz}$, $f_p = 0.543$, $f_z = 2.14$, $Q = 0.841$, $f'_p = 0.987$, $f'_z = 4.92$, $Q' = 4.403$, normalized to ripple BW

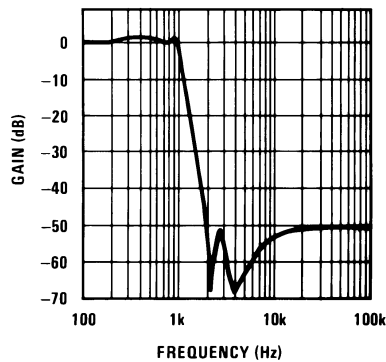
$$f = \frac{1}{2\pi R1C1} \times \sqrt{K}, K = \frac{R4R5}{R3} \left(\frac{1}{r_{DS}} + \frac{1}{R4} + \frac{1}{R5} \right), r_{DS} \approx \frac{R_{ON}}{\left(1 - \frac{V_{GS}}{V_P} \right)^{1/2}}$$

Use the BP outputs to tune Q, Q', tune the 2 sections separately

$R1 = R2 = 92.6k$, $R3 = R4 = R5 = 100k$, $R6 = 10k$, $R0 = 107.8k$, $R_L = 100k$, $R_H = 155.1k$,

$R'1 = R'2 = 50.9k$, $R'4 = R'5 = 100k$, $R'6 = 10k$, $R'0 = 5.78k$, $R'_L = 100k$, $R'_H = 248.12k$, $R'_f = 100k$. All capacitors are $0.001 \mu F$.

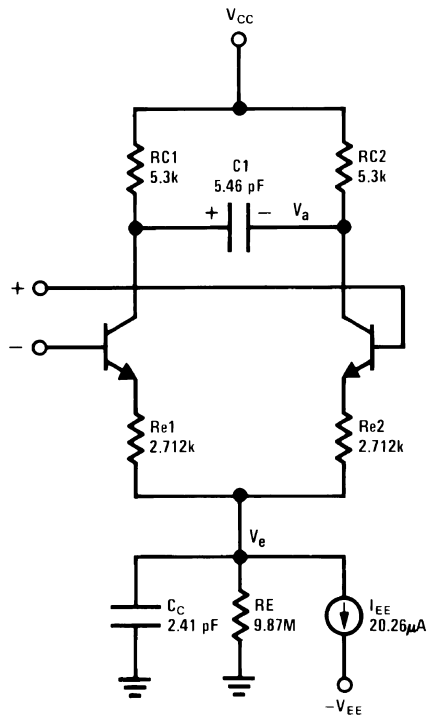
Lowpass Response



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Typical Simulation

LM148, LM741 Macromodel for Computer Simulation

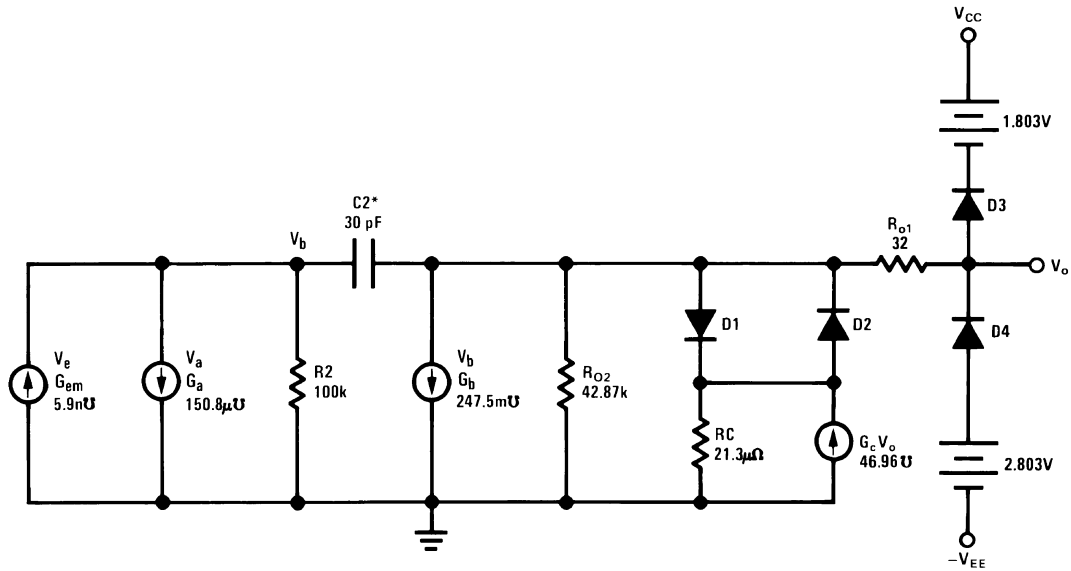


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For more details, see IEEE Journal of Solid-State Circuits, Vol. SC-9, No. 6, December 1974

Note 6: $\omega_1 = 112|S = 8 \times 10^{-16}$

Note 7: $\omega_2 = 144 \cdot C2 = 6 \text{ pF}$ for LM149



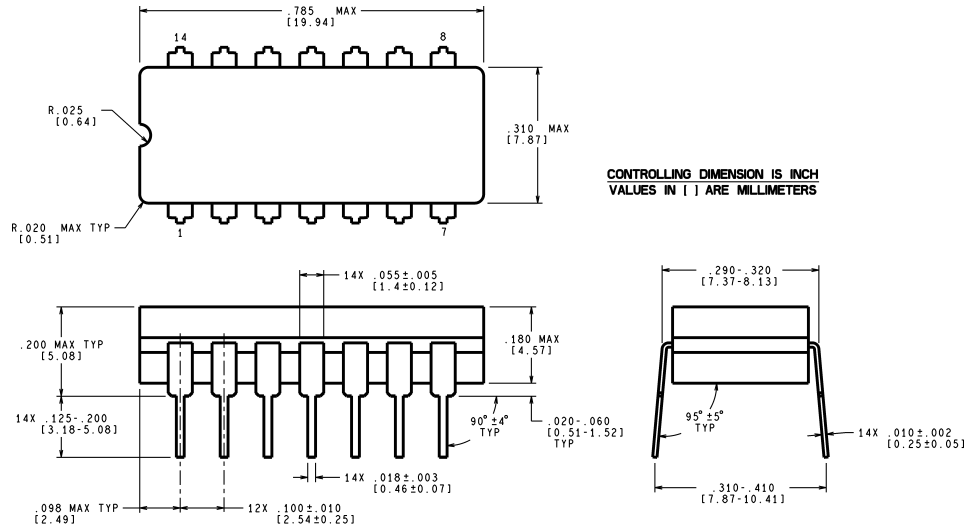
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Revision History Section

| Date Released | Revision | Section | Originator | Changes |
|---------------|----------|-------------------------------|------------|--|
| 02/08/05 | A | New Release, Corporate format | L. Lytle | 1 MDS data sheet converted into one Corp. data sheet format. MNLM148-X, Rev. 2A2. MDS data sheet will be archived. |

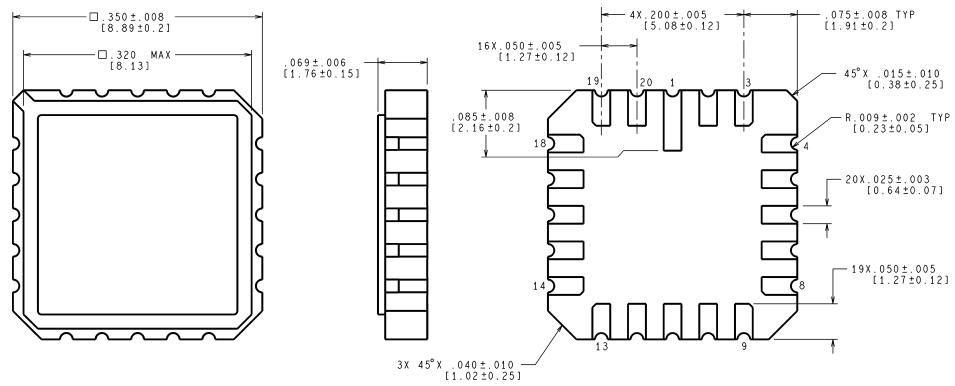
Physical Dimensions inches (millimeters)

unless otherwise noted



J14A (Rev J)

Ceramic Dual-In-Line Package (J) NS Package Number J14A



E20A (Rev F)

Leadless Chip Carrier(E) NS Package Number E20A

Notes

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.

For the most current product information visit us at www.national.com.

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

- | | |
|--|---|
| <p>1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.</p> | <p>2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.</p> |
|--|---|

BANNED SUBSTANCE COMPLIANCE

National Semiconductor manufactures products and uses packing materials that meet the provisions of the Customer Products Stewardship Specification (CSP-9-111C2) and the Banned Substances and Materials of Interest Specification (CSP-9-111S2) and contain no "Banned Substances" as defined in CSP-9-111S2.



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